

FIG. 1A

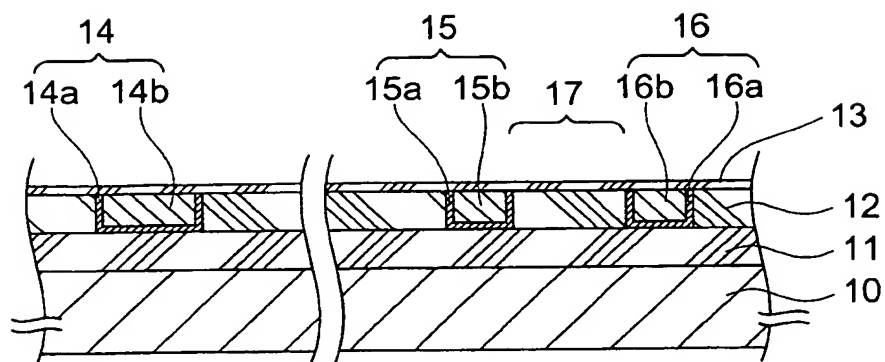
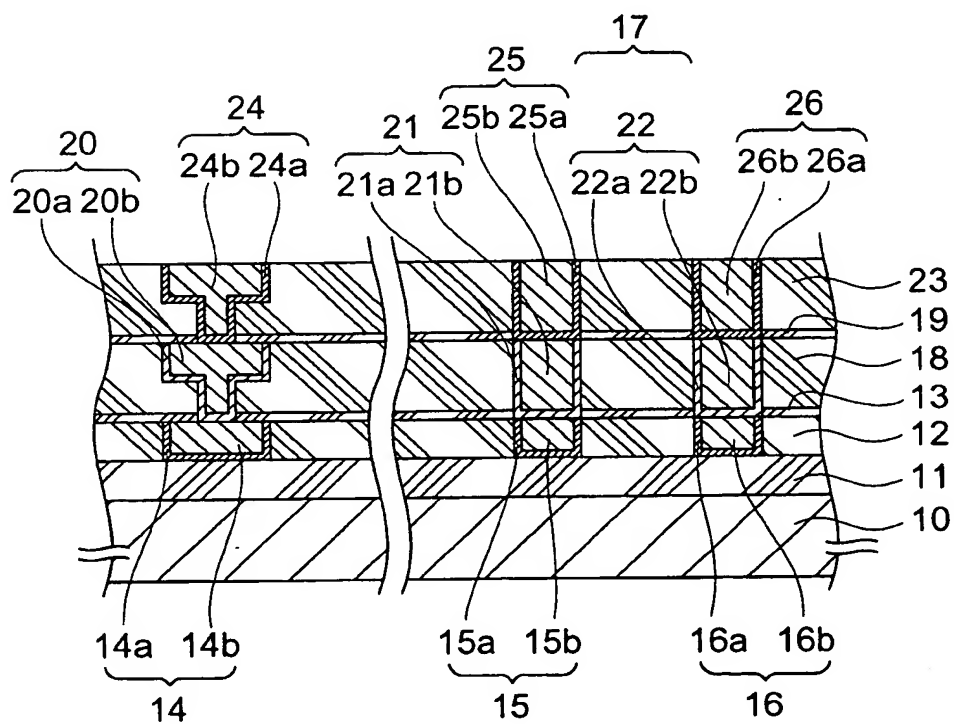
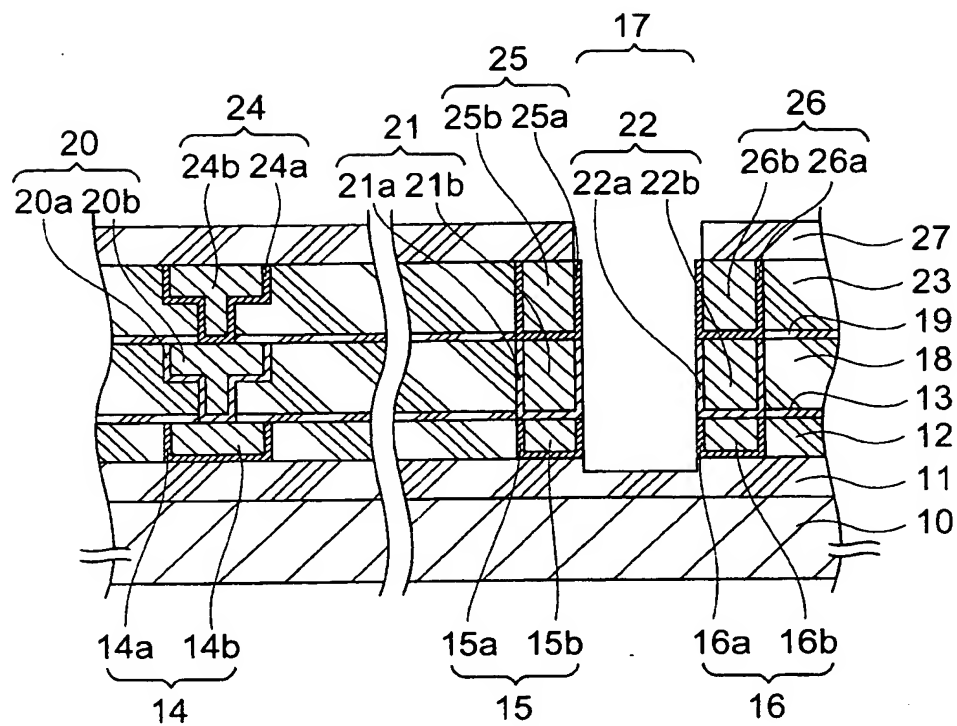


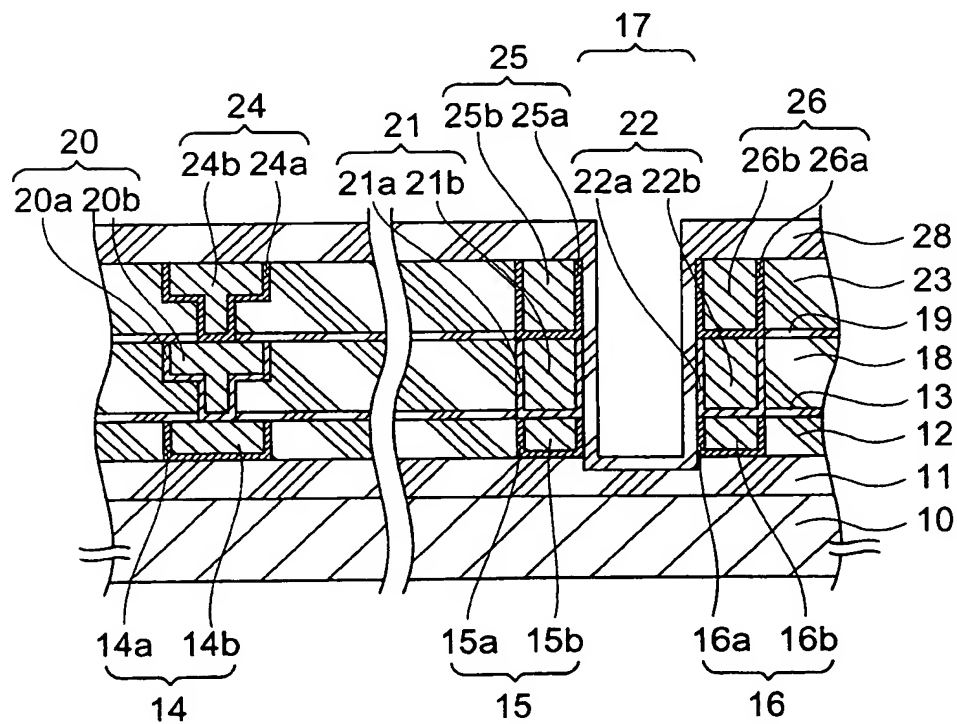
FIG. 1B



# FIG. 2A



# FIG. 2B



A detailed cross-sectional view of a multi-layered structure, likely a semiconductor device or a composite material. The structure is composed of several horizontal layers, with the bottom layer labeled 10. Above layer 10, there are three main vertical sections or regions, each containing a central vertical feature. The leftmost region is labeled 14, with sub-components 14a and 14b. The middle region is labeled 15, with sub-components 15a and 15b. The rightmost region is labeled 16, with sub-components 16a and 16b. The central vertical features in these regions are labeled 20, 21, and 22 respectively. The top of the structure is labeled 23, and the bottom of the central features is labeled 24. The structure is divided into three main vertical sections by vertical lines, with the left section labeled 17, the middle section labeled 18, and the right section labeled 19. The rightmost section is further divided into sub-components 25a and 25b. The structure is also divided into horizontal layers, with the top layer labeled 26, the middle layer labeled 27, and the bottom layer labeled 28. The structure is also divided into vertical sections, with the left section labeled 29, the middle section labeled 30, and the right section labeled 31. The structure is also divided into horizontal layers, with the top layer labeled 32, the middle layer labeled 33, and the bottom layer labeled 34.

FIG. 4

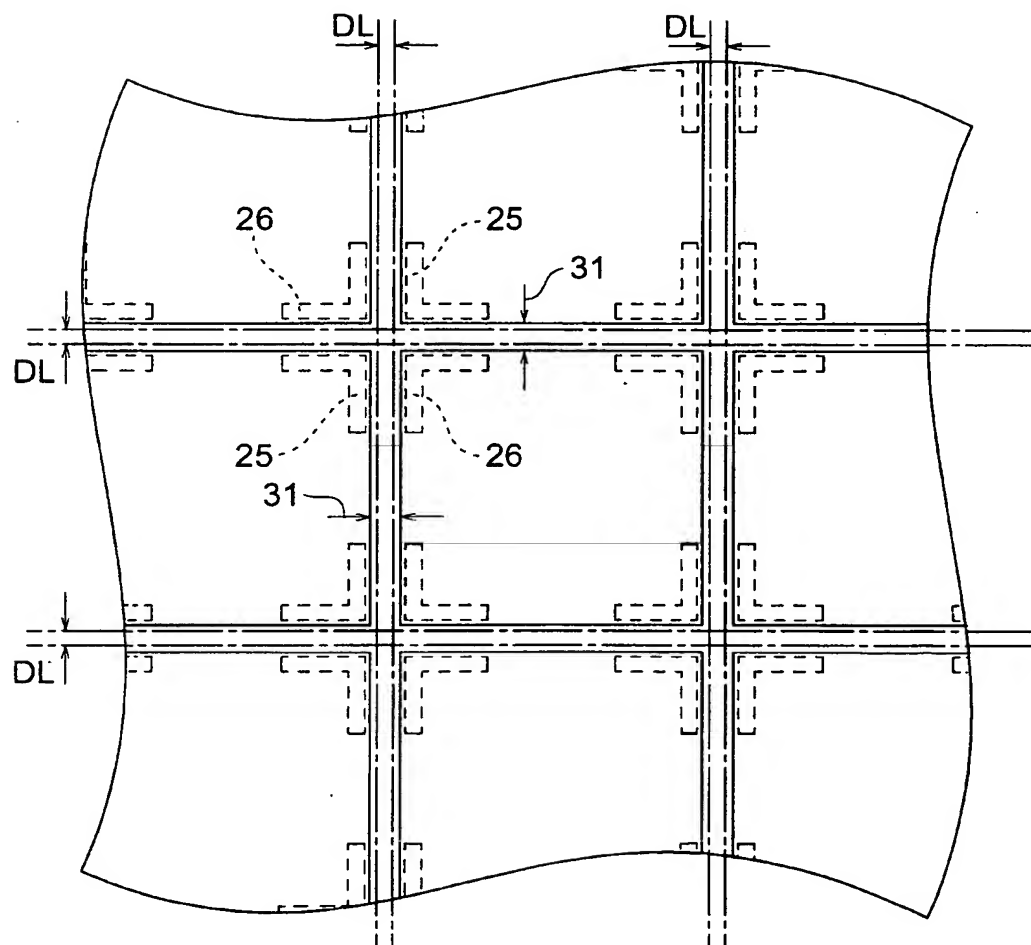
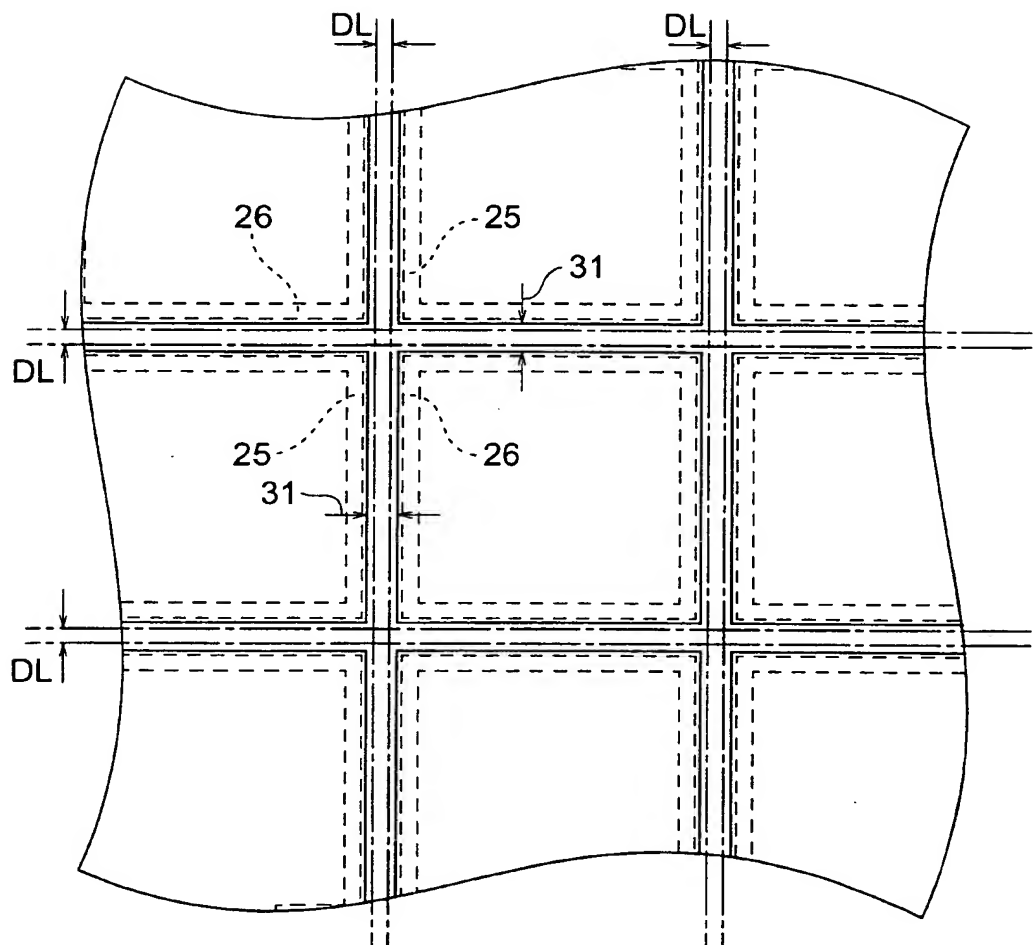
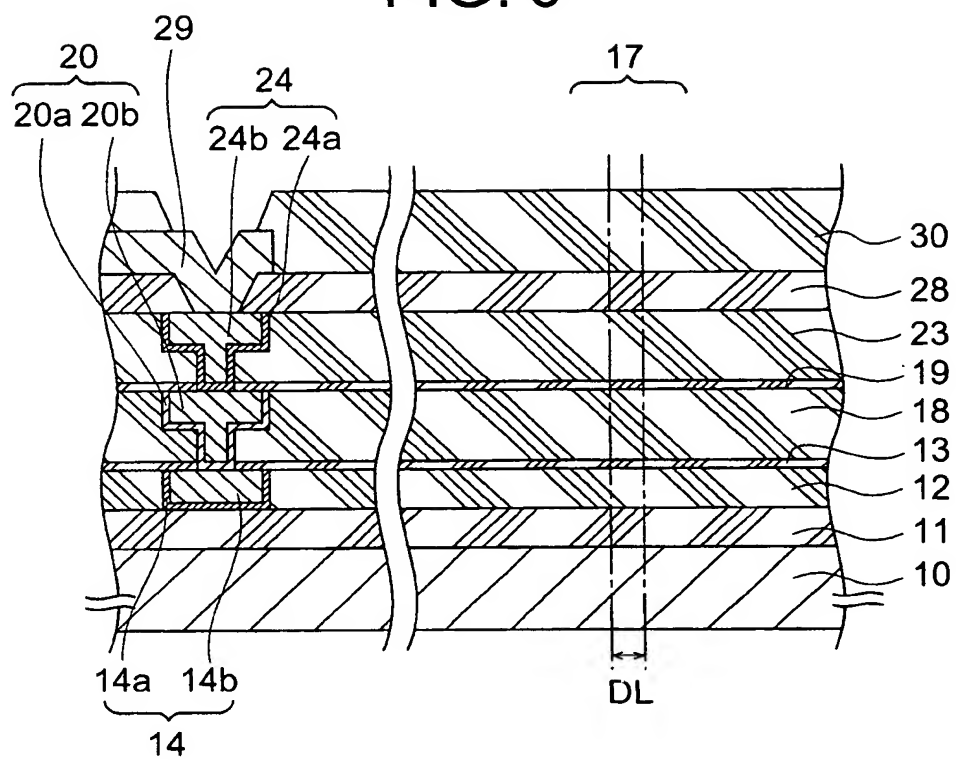


FIG. 5



# FIG. 6



# FIG. 7

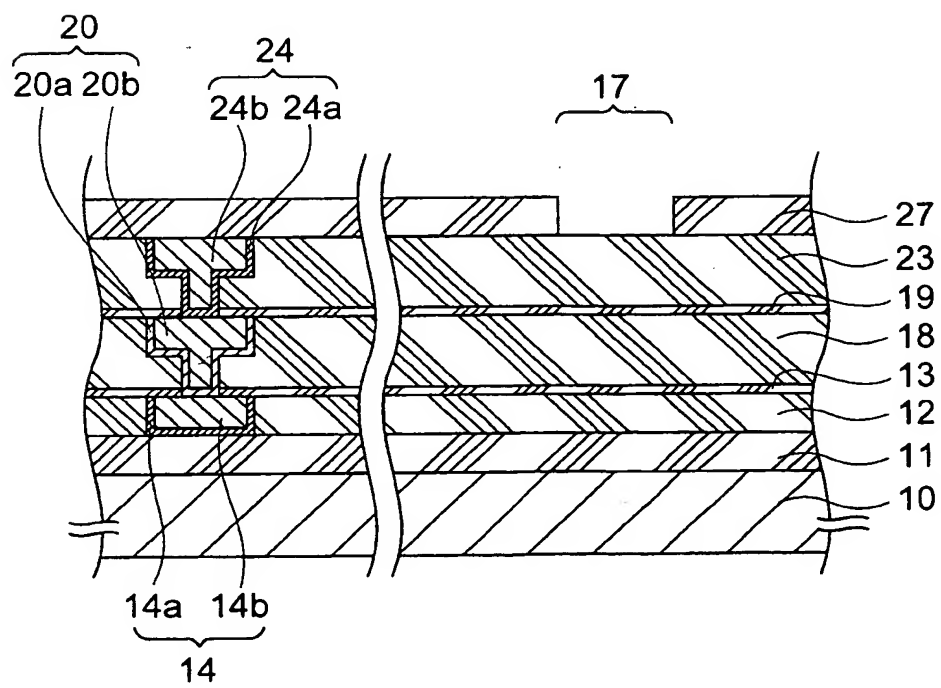
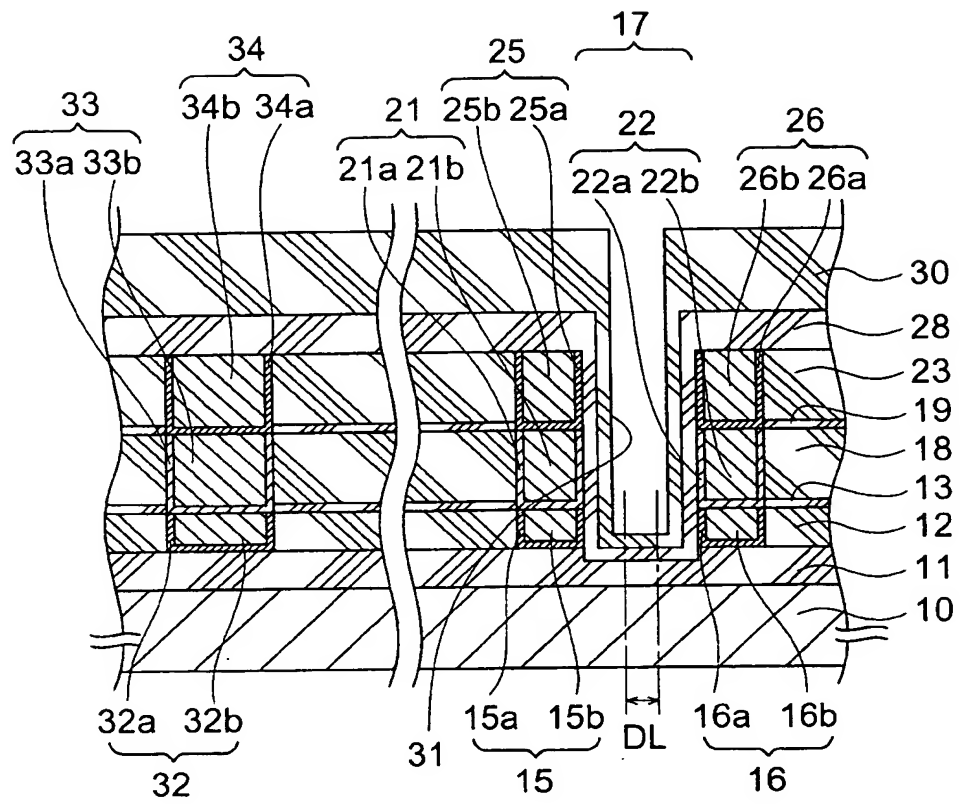


FIG. 8



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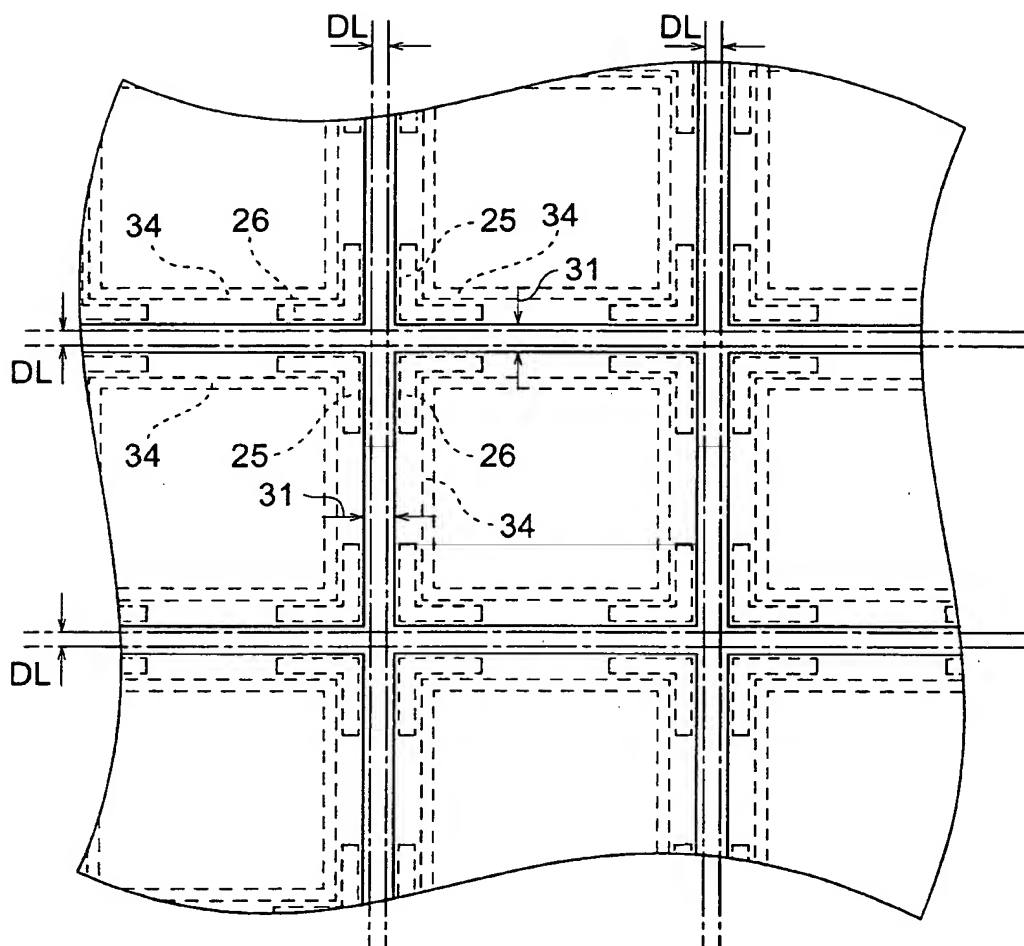




FIG. 10A

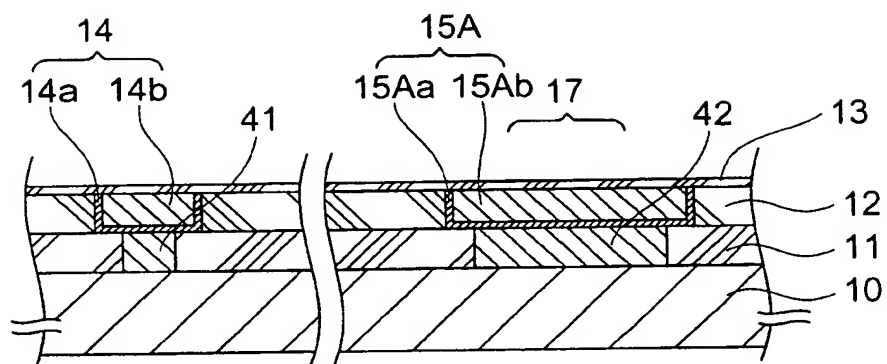


FIG. 10B

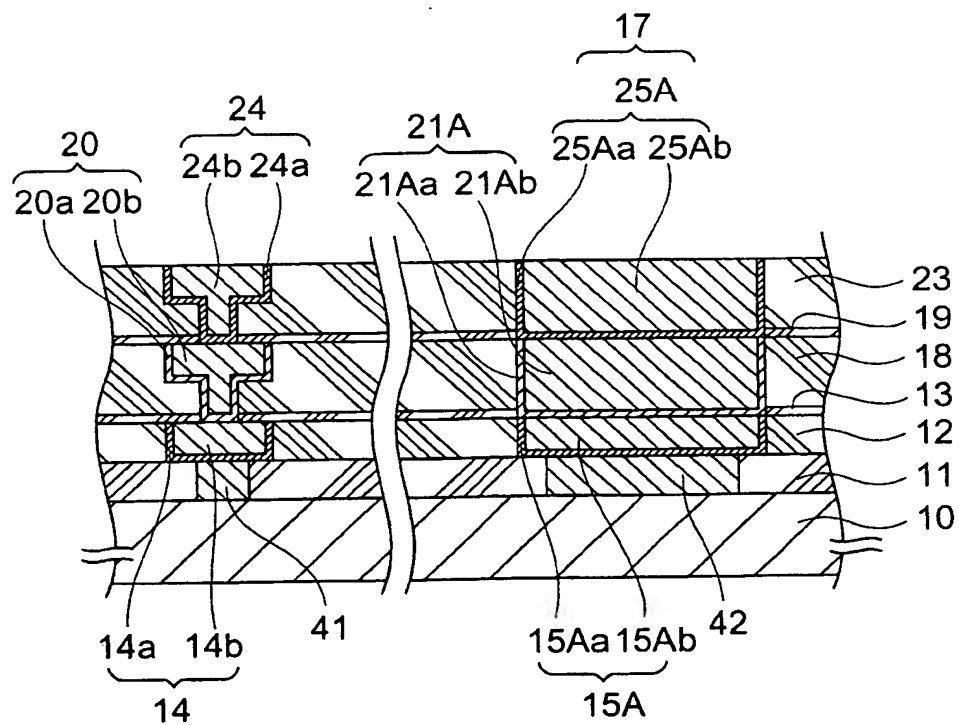


FIG. 11A

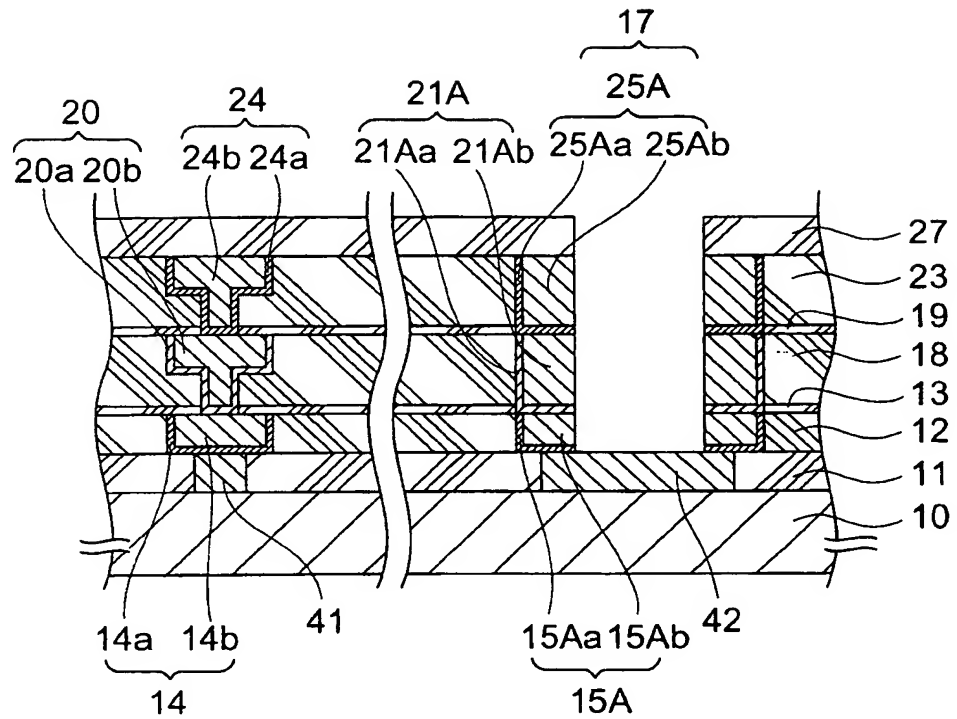
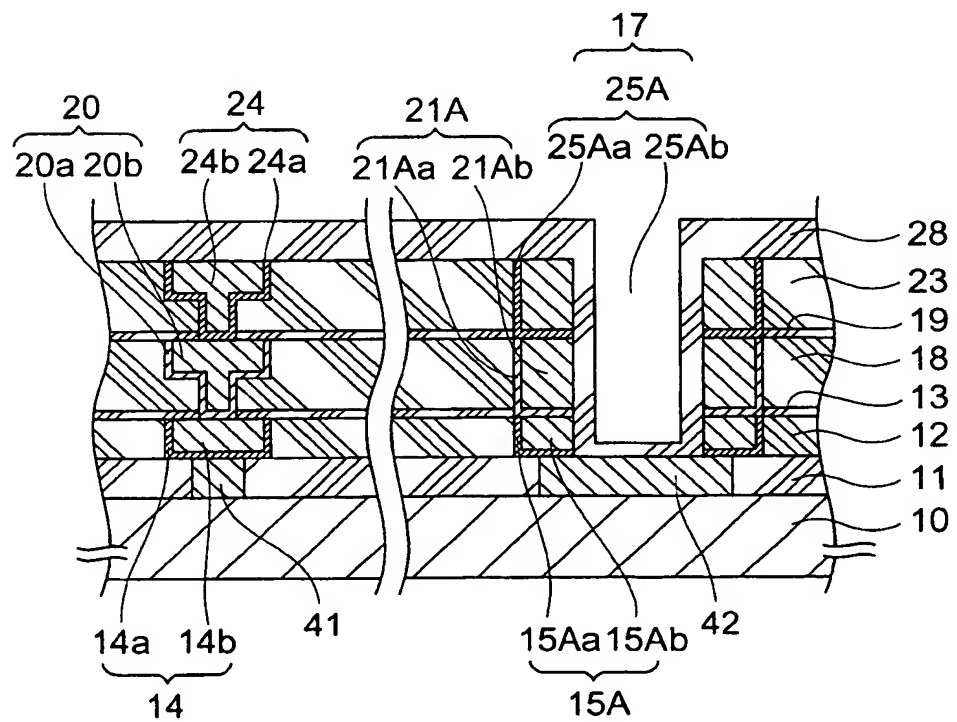
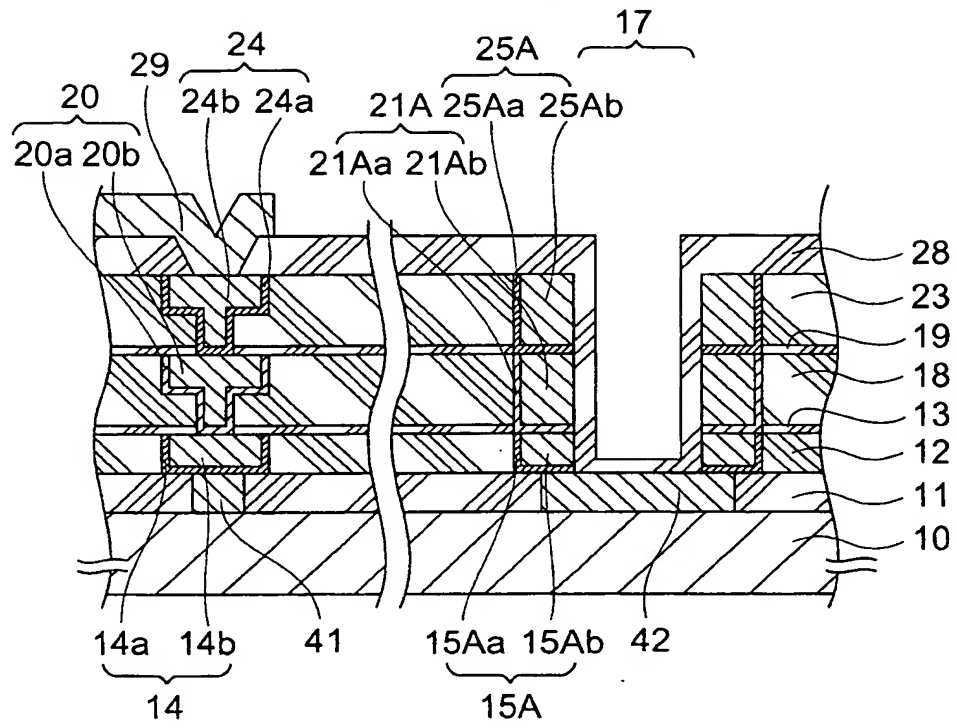


FIG. 11B



# FIG. 12A



# FIG. 12B

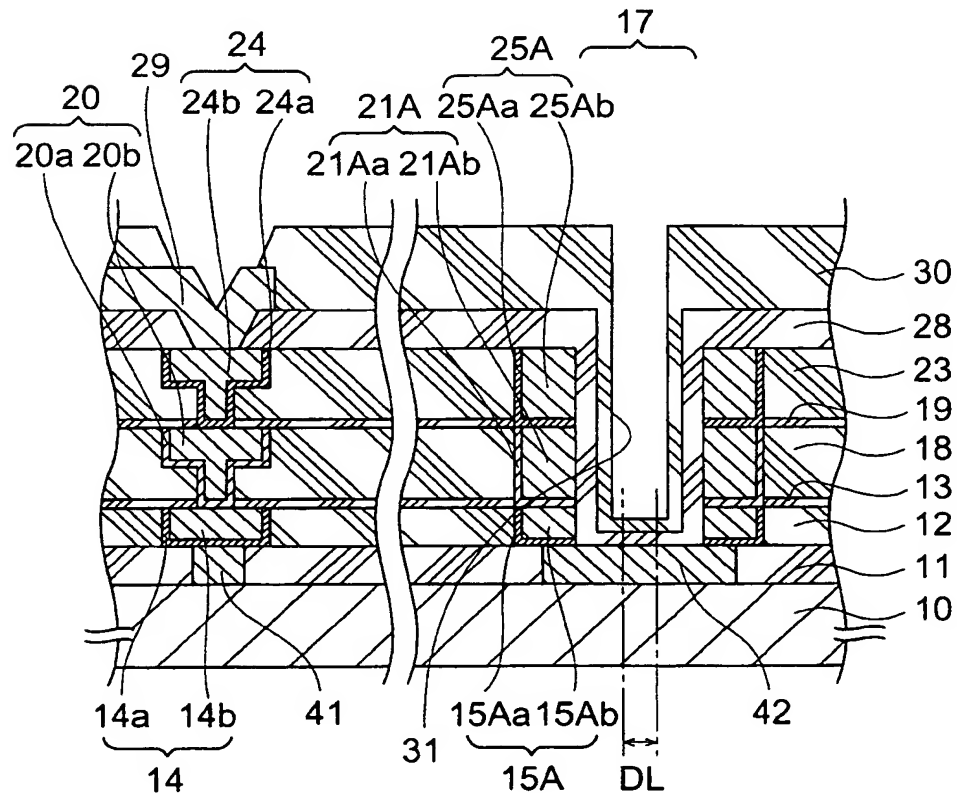


FIG. 13

